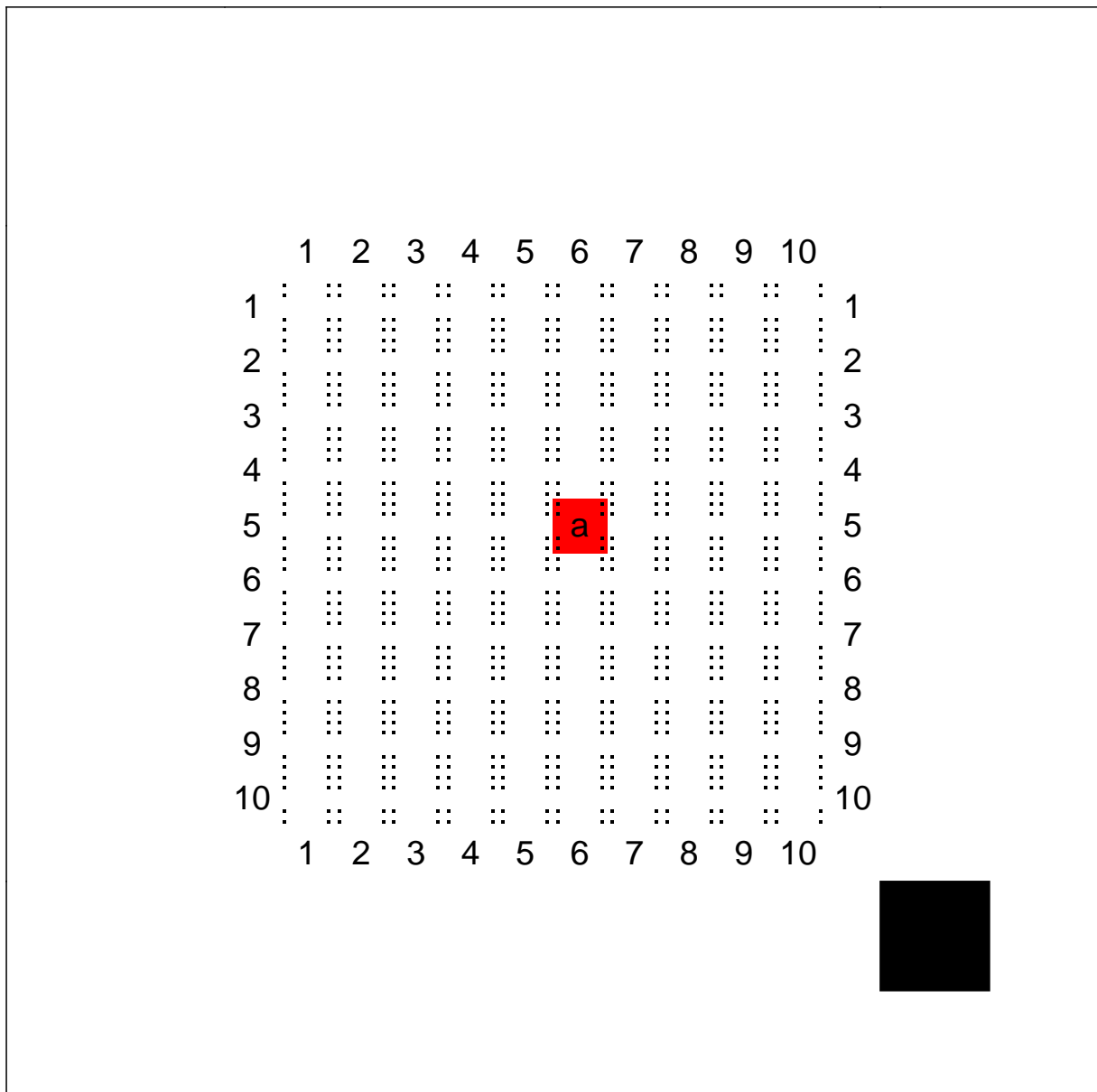


Sample # c193

Substrate	type	Si	orientation	<100>	thickness	650 μm	size	20 mm x 20 mm
	doping	p-type (boron)			resistivity	0.001-0.007 Ohm cm		
Top layer	type	SiO2 (dry thermal oxidation)					thickness	90 nm
Crystallite	name: area (# of layers)		a: 1250 μm^2 (1)					

Sample Map



Graphene crystallite a

